

IN THE CLAIMS

Please amend the claims as follows:

1. (Currently Amended) A semiconductor laser device, comprising:
a semiconductor laser element arranged inside an airtight-sealed package, the semiconductor laser element having an active region formed of a gallium nitride-based crystal, wherein a rated output power of the semiconductor laser device is 30 mW or more, and an atmospheric gas inside the package is a mixture of oxygen and nitrogen, with an oxygen content of more than 20% ~~or more~~.
2. (Original) The semiconductor laser device of claim 1, wherein the semiconductor laser element has a dielectric oxide film formed on a laser emission surface thereof.
3. (Cancelled)
4. (Original) The semiconductor laser device of claim 1, wherein the semiconductor laser element emits light having a wavelength of 0.9 μm or less.
5. (Currently Amended) The semiconductor laser device of claim 1, ~~A semiconductor laser device, comprising:~~
~~a semiconductor laser element arranged inside an airtight-sealed package, the semiconductor laser element having an active region formed of a gallium nitride-based crystal,~~
~~wherein a rated output power of the semiconductor laser device is 30 mW or more, and~~

~~an~~ the atmospheric gas inside the package is dry air.

6. (Cancelled)

7. (Cancelled)

8. (Cancelled)

9. (Previously Presented) The semiconductor laser device of claim 1, wherein the gallium nitride-based crystal is an AlGaN- or InGaN-based crystal.